



EXPRESS MAIL NO. EL897860072US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Paolo Menegoli
Application No. : 09/659,885
Filed : September 12, 2000
For : DMOS TRANSISTORS WITH SCHOTTKY
DIODE BODY STRUCTURE

Examiner : Steven Loke
Art Unit : 2811
Docket No. : 850063.498C1
Date : February 25, 2002

Commissioner for Patents
Washington, DC 20231

TECHNOLOGY CENTER 2800

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AMENDMENT

Commissioner for Patents:

In response to the Office Action mailed October 24, 2001, please extend the period of time for response one month, to expire on February 24, 2002. Enclosed are a Petition for an Extension of Time and the requisite fee.

In response to the Office Action mailed October 24, 2001, Applicant respectfully requests that the above-identified application be amended as follows:

In the Claims:

Please amend claim 17 to read as follows:

17. (Amended) A method of operating a DMOS transistor having a drain of first conductivity formed in an [expitaxial] layer of same conductivity, a body formed of second conductivity in the epitaxial layer, a source of first conductivity in the body, a gate electrode positioned above the source, the body, and the epitaxial layer, a conductive contact coupled to the

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